

TOSHIBA FIELD EFFECT TRANSISTOR SILICON P CHANNEL MOS TYPE

2SJ338

AUDIO FREQUENCY POWER AMPLIFIER APPLICATION

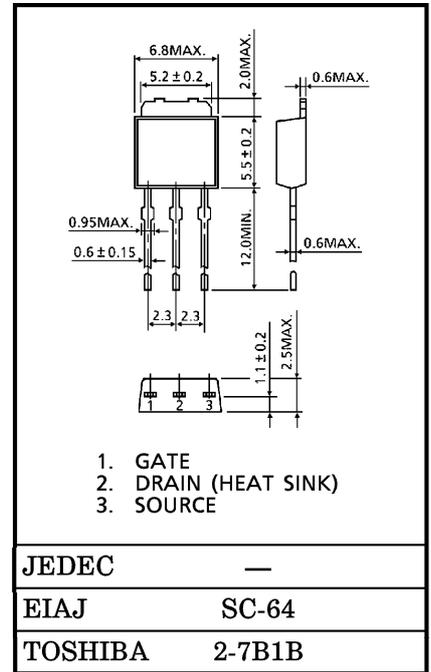
INDUSTRIAL APPLICATIONS

Unit in mm

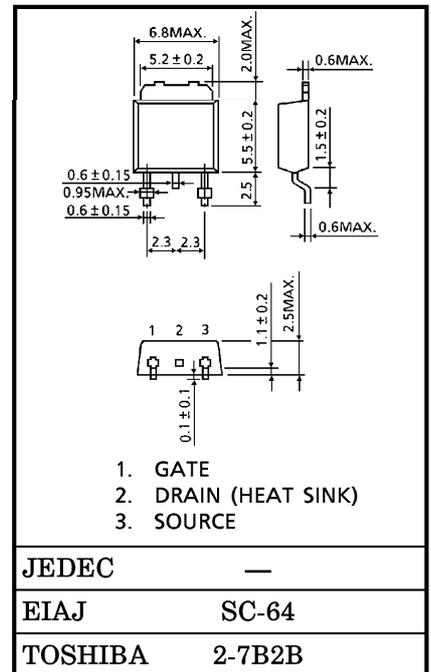
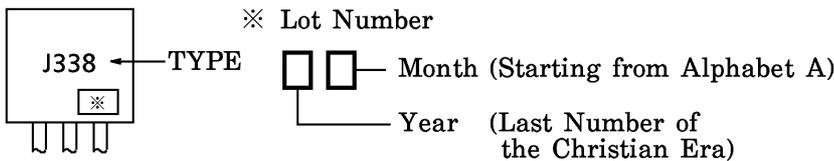
- High Breakdown Voltage : $V_{DSS} = -180\text{ V}$
- High Forward Transfer Admittance : $|Y_{fs}| = 0.7\text{ S (Typ.)}$
- Complementary to 2SK2162

MAXIMUM RATINGS ($T_a = 25^\circ\text{C}$)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Drain-Source Voltage	V_{DSS}	-180	V
Gate-Source Voltage	V_{GSS}	± 20	V
Drain Current	I_D	-1	A
Power Dissipation ($T_c = 25^\circ\text{C}$)	P_D	20	W
Channel Temperature	T_{ch}	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-55~150	$^\circ\text{C}$



MARKING



Weight : 0.36 g

961001EAA2

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ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Gate Leakage Current	I _{GSS}	V _{DS} = 0, V _{GS} = ±20 V	—	—	±100	nA
Drain-Source Breakdown Voltage	V _{(BR)DSS}	I _D = -10 mA, V _{GS} = 0	-180	—	—	V
Gate-Source Cut-off Current	V _{GS(OFF)} (Note)	V _{DS} = -10 V, I _D = -10 mA	-0.8	—	-2.8	V
Drain-Source Saturation Voltage	V _{DS(ON)}	I _D = -0.6 A, V _{GS} = -10 V	—	-1.2	-3.0	V
Forward Transfer Admittance	Y _{fs}	V _{DS} = -10 V, I _D = -0.3 A	—	0.7	—	S
Input Capacitance	C _{iss}	V _{DS} = -10 V, V _{GS} = 0, f = 1 MHz	—	210	—	pF
Output Capacitance	C _{oss}	V _{DS} = -10 V, V _{GS} = 0, f = 1 MHz	—	90	—	pF
Reverse Transfer Capacitance	C _{rss}	V _{DS} = -10 V, V _{GS} = 0, f = 1 MHz	—	45	—	pF

(Note) : V_{GS(OFF)} Classification O : -0.8~-1.6, Y : -1.4~-2.8

**This transistor is the electrostatic sensitive device.
Please handle with caution.**